

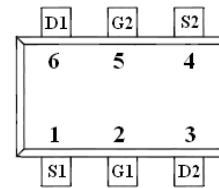
### ➤ General Description

This PAN3034EL Dual N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent  $R_{ds(On)}$  performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

### ➤ Feature

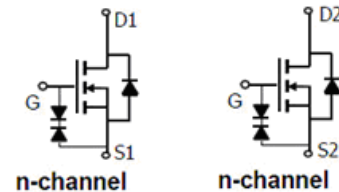
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- ESD Protection
- Low Battery Voltage Operation
- SOT-563 package design

### ➤ SOT-563



### ➤ Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Smart Phones, Paggers



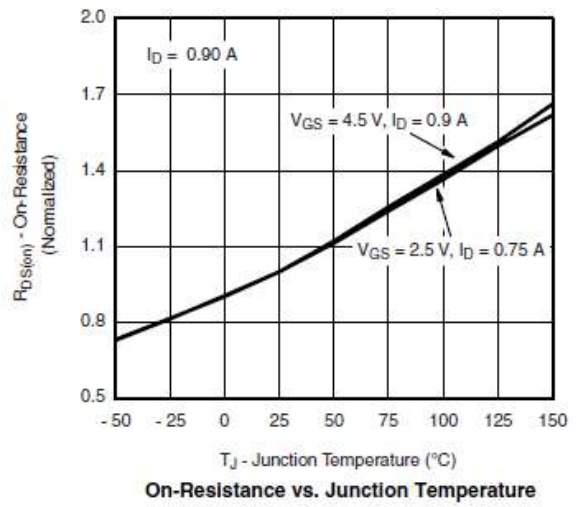
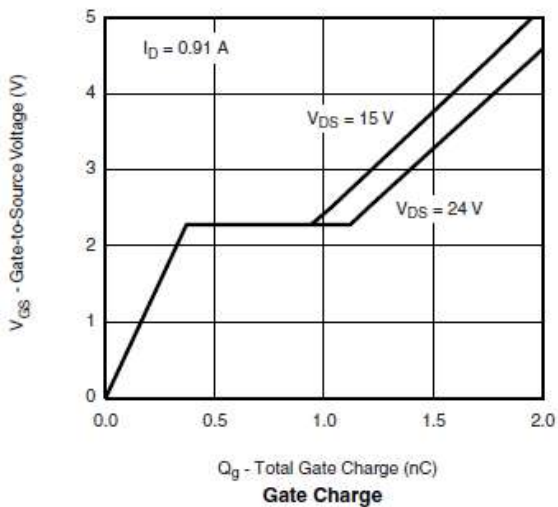
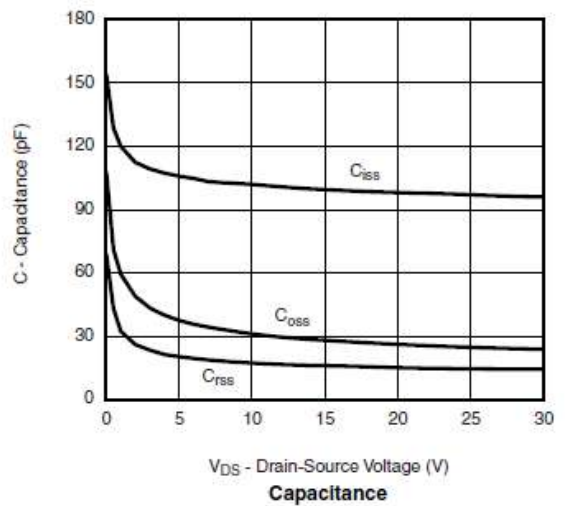
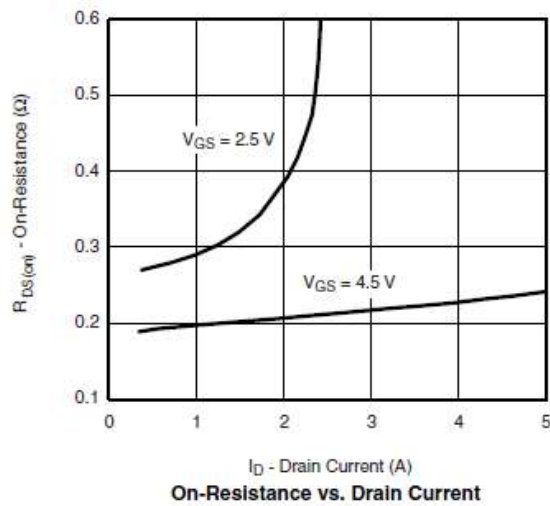
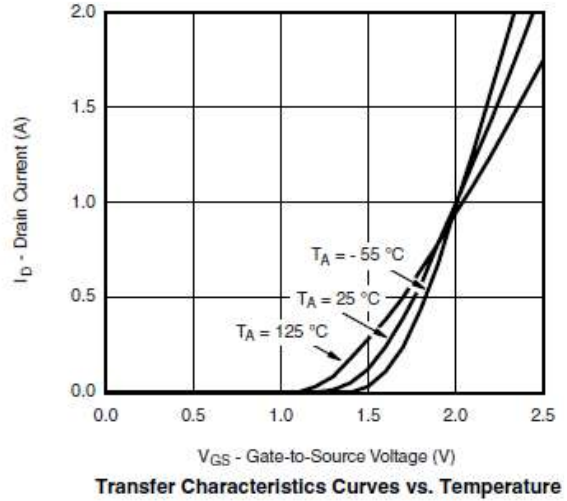
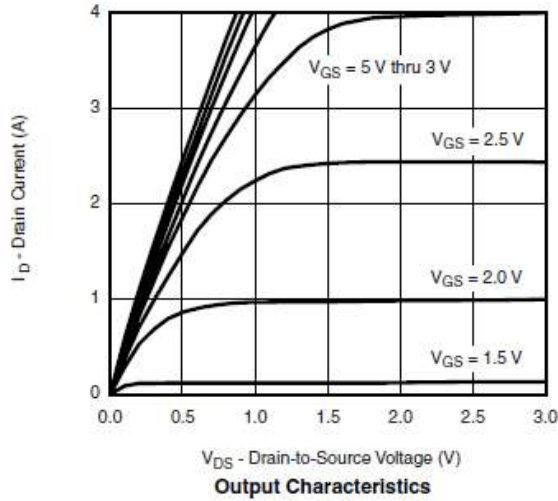
### ➤ Absolute Maximum Ratings

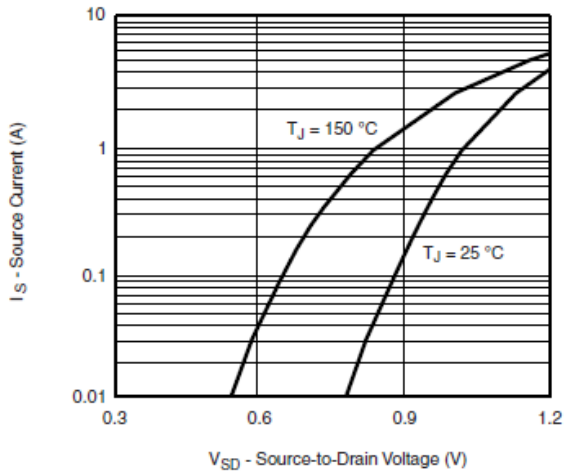
Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	30	V
Gate –Source Voltage	$V_{GSS}$	$\pm 12$	V
Continuous Drain Current( $T_J=150^\circ C$ )	$I_D$	$T_A=25^\circ C$	0.7
		$T_A=70^\circ C$	0.4
Pulsed Drain Current	$I_{DM}$	1.0	A
Continuous Source Current(Diode Conduction)	$I_S$	0.3	A
Power Dissipation	$P_D$	$T_A=25^\circ C$	0.27
		$T_A=70^\circ C$	0.16
Operating Junction Temperature	$T_J$	-55/150	$^\circ C$
Storage Temperature Range	$T_{STG}$	-55/150	$^\circ C$

➤ Electrical Characteristics ( $T_A=25^\circ C$  Unless otherwise noted)

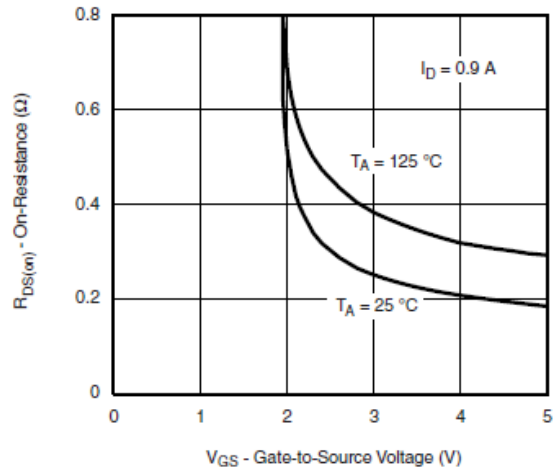
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5		1.5	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$			$\pm 5$	mA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=24V, V_{GS}=0V$			1	uA
		$V_{DS}=24V, V_{GS}=0V$ $T_J=85^\circ C$			5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=4.5V$	0.7			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.6A$		400	450	m $\Omega$
		$V_{GS}=2.5V, I_D=0.5A$		550	600	
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=0.4A$		1		S
Diode Forward Voltage	$V_{SD}$	$I_S=0.15A, V_{GS}=0V$		0.6	1.2	V
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V$ $f=1MHz$		85		pF
Output Capacitance	$C_{oss}$			25		
Reverse Transfer Capacitance	$C_{riss}$			15		
Total Gate Charge	$Q_g$	$V_{DS}=15V, V_{GS}=4.5V$ $I_D=0.6A$		1.4	1.8	nC
Gate-Source Charge	$Q_{gs}$			0.3		
Gate-Drain Charge	$Q_{gd}$			0.6		
Turn-On Time	$t_{d(on)}$	$V_{DD}=15V, R_L=20\Omega$ $I_D=0.5A, V_{GEN}=4.5V$ $R_G=1\Omega$		15	25	ns
	$t_r$			25	45	
Turn-Off Time	$t_{d(off)}$			15	25	
	$t_f$			10	20	

### ➤ Typical Characteristics

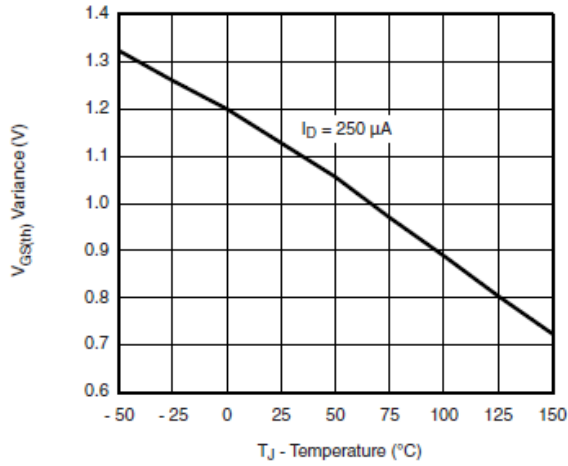




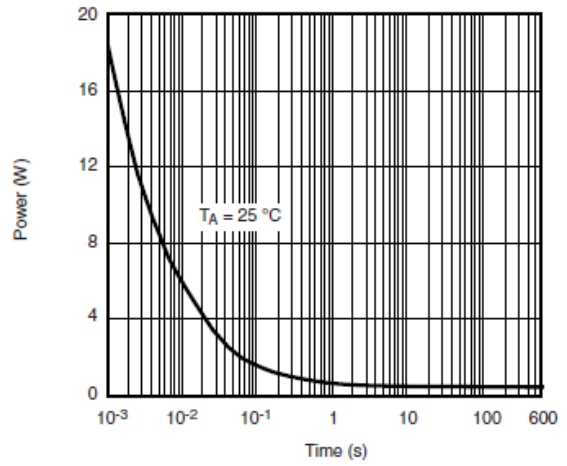
Forward Diode Voltage vs. Temperature



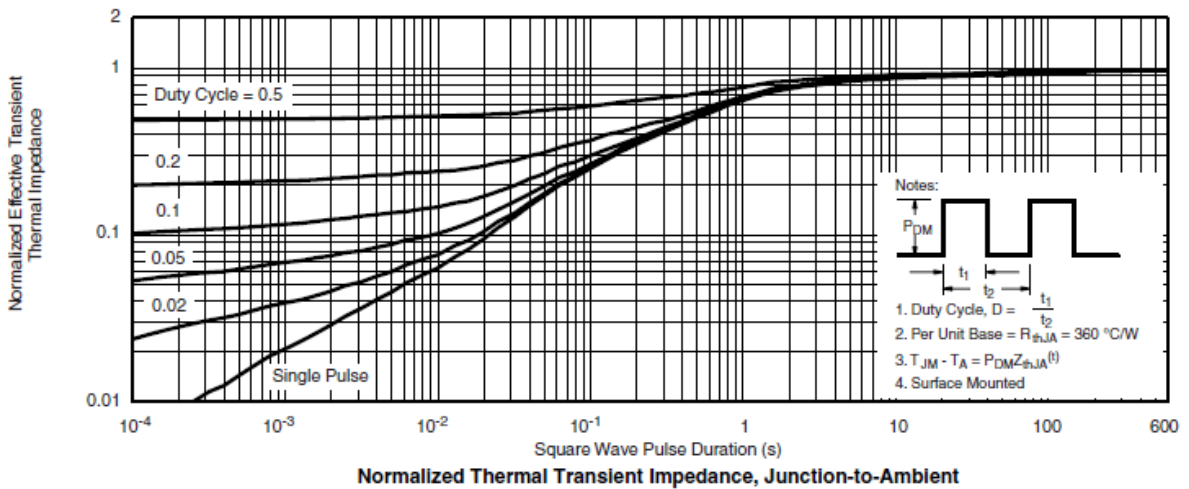
$R_{DS(on)}$  vs.  $V_{GS}$  vs. Temperature



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

### ➤ Recommand IR Reflow Soldering Thermal Profile

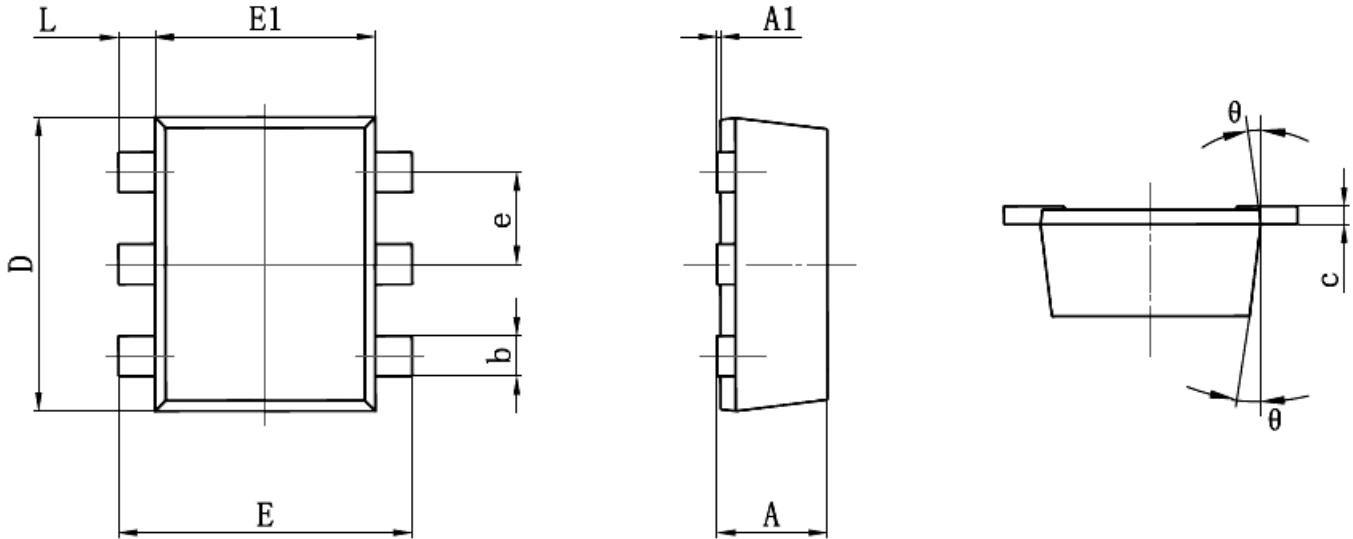


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T <sub>smin</sub> )	150°C
Temperature Max. (T <sub>smax</sub> )	200°C
Time (t <sub>s</sub> ) from (T <sub>smin</sub> to T <sub>smax</sub> )	60-120 seconds
Average Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

### ➤ Ordering Information

Part Number	Description	Quantity
PAN3034EL	SOT-563 Reel	3000 pcs

➤ Package Information ( SOT-563 )



Symbol	Dimenslons In Millimeters		Dimenslons In Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
$\theta$	7 °REF.		7 °REF.	

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